

SOT-363

Pin Definition:

- 1. Drain 6. Drain
- 2. Drain 5. Drain
- 3. Gate 4. Source

Features

- Advance Trench Process Technology
- PWM Optimized

Application

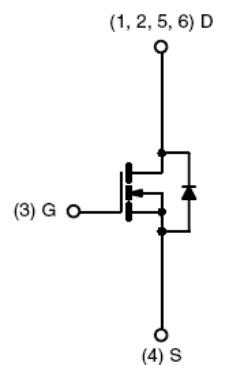
- Boost Converter in Portable devices
- Low Current Synchronous Rectifier

Ordering Information

Part No.	Package	Packing
TSM1424CU6 RF	SOT-363	3Kpcs / 7" Reel

PRODUCT SUMMARY

V_{DS} (V)	R_{DS(on)}(mΩ)	I_D (A)
20	75 @ V _{GS} = 10V	3.6
	115 @ V _{GS} = 4.5V	2.9

Block Diagram

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current		I _D	3.6	A
Pulsed Drain Current		I _{DM}	10	A
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	1.3	A
Maximum Power Dissipation	T _a = 25°C	P _D	1.6	W
	T _a = 75°C		0.8	
Operating Junction Temperature		T _J	+150	°C
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Thermal Performance

Parameter		Symbol	Limit	Unit
Junction to Case Thermal Resistance		R<θ _{JF}	45	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)		R<θ _{JA}	80	°C/W

Notes:

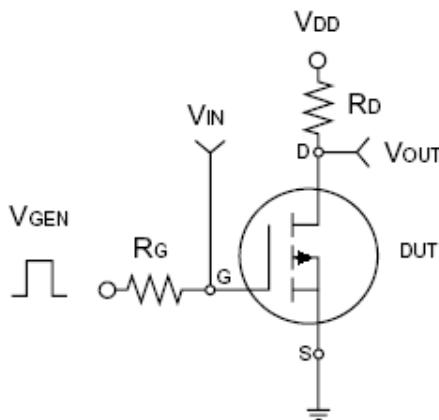
- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.

Electrical Specifications ($T_a = 25^\circ\text{C}$ unless otherwise noted)

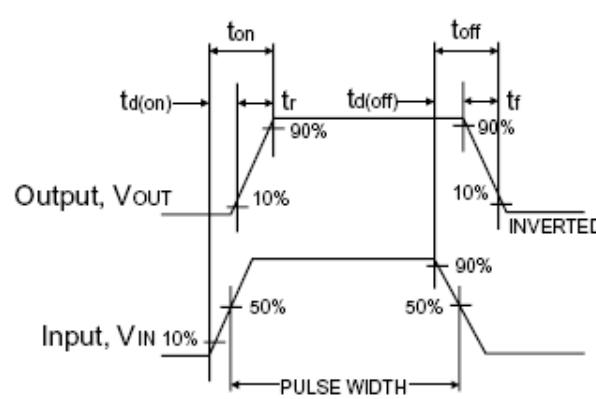
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	BV_{DSS}	30	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	$V_{GS(\text{TH})}$	0.8	--	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 24\text{V}$, $V_{GS} = 0\text{V}$	I_{DSS}	--	--	1.0	μA
On-State Drain Current	$V_{DS} \geq 10\text{V}$, $V_{GS} = 4.5\text{V}$	$I_{D(\text{ON})}$	10	--	--	A
Drain-Source On-State Resistance	$V_{GS} = 10\text{V}$, $I_D = 3.6\text{A}$	$R_{DS(\text{ON})}$	--	61	75	$\text{m}\Omega$
	$V_{GS} = 4.5\text{V}$, $I_D = 2.9\text{A}$		--	92	115	
Forward Transconductance	$V_{DS} = 10\text{V}$, $I_D = 3.6\text{A}$	g_{fs}	--	5	--	S
Diode Forward Voltage	$I_S = 1.3\text{A}$, $V_{GS} = 0\text{V}$	V_{SD}	--	0.8	1.2	V
Dynamic^b						
Total Gate Charge	$V_{DS} = 15\text{V}$, $I_D = 3.6\text{A}$, $V_{GS} = 4.5\text{V}$	Q_g	--	1.9	3	nC
Gate-Source Charge		Q_{gs}	--	0.75	--	
Gate-Drain Charge		Q_{gd}	--	0.75	--	
Input Capacitance	$V_{DS} = 15\text{V}$, $V_{GS} = 0\text{V}$, $f = 1.0\text{MHz}$	C_{iss}	--	190	--	pF
Output Capacitance		C_{oss}	--	100	--	
Reverse Transfer Capacitance		C_{rss}	--	55	--	
Switching^c						
Turn-On Delay Time	$V_{DD} = 15\text{V}$, $R_L = 15\Omega$, $I_D = 1\text{A}$, $V_{GEN} = 10\text{V}$, $R_G = 6\Omega$	$t_{d(on)}$	--	10	15	nS
Turn-On Rise Time		t_r	--	12	18	
Turn-Off Delay Time		$t_{d(off)}$	--	15	22	
Turn-Off Fall Time		t_f	--	9	15	

Notes:

- a. pulse test: PW $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

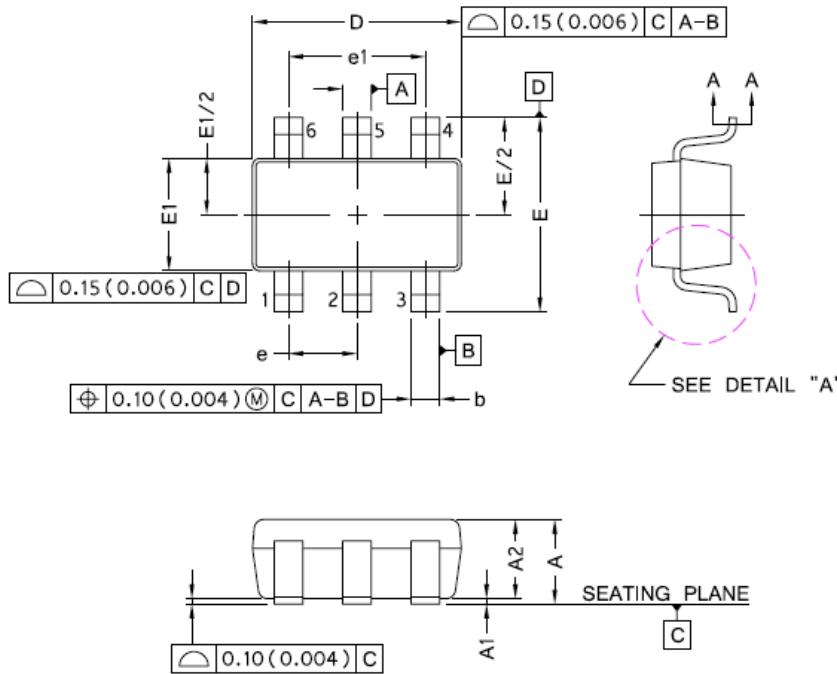


Switching Test Circuit



Switching Waveforms

SOT-363 Mechanical Drawing



SOT-363 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX.
A	0.80	1.10	0.031	0.043
A1	0	0.10	0	0.004
A2	0.80	1.00	0.031	0.040
b	0.15	0.30	0.006	0.012
b1	0.15	0.25	0.006	0.010
c	0.08	0.22	0.003	0.009
c1	0.08	0.20	0.003	0.008
D	1.90	2.10	0.074	0.084
E	2.00	2.20	0.078	0.086
E1	1.15	1.35	0.045	0.055
e	0.65 BSC		0.025 BSC	
e1	1.30 BSC		0.051 BSC	
L	0.26	0.46	0.010	0.018
θ	0°	8°	0°	8°
θ1	4°	10°	4°	10°

